优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码

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Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

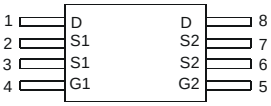
Mechanical Data

- Case: TSSOP-8L
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.039 grams (approximate)

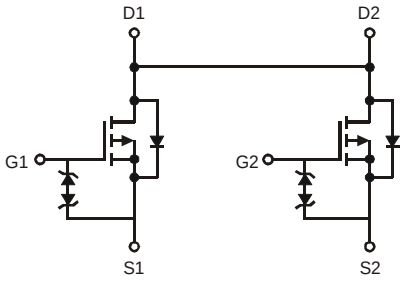
ESD PROTECTED TO 3kV

TOP VIEW

BOTTOM VIEW



Top View
Pin Configuration



Internal Schematic

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current (Note 3)	Steady State	T_A = 25°C T_A = 85°C	I_D	6.04 3.96	A
Pulsed Drain Current (Note 4)			I_{DM}	22	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P_D	0.89	W
Thermal Resistance, Junction to Ambient @T_A = 25°C	$R_{\theta JA}$	142.7	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes: 1. No purposefully added lead.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	-	-	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current	I_{DSS}	-	-	-1.0	μA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±10	μA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.4	-0.7	-1.0	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	-	23	35	mΩ	V_{GS} = -4.5V, I_D = -4.0A
			30	45		V_{GS} = -2.5V, I_D = -4.0A
			41	62		V_{GS} = -1.8V, I_D = -2.0A
Forward Transfer Admittance	$\|Y_{fs}\|$	-	14	-	S	V_{DS} = -5V, I_D = -4A
Diodes Forward Voltage	V_{SD}	-	-0.7	-1.0	V	Is = -1A, V_{GS} = 0V
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C_{iss}	-	1610	-	pF	V_{DS} = -10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	157	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	145	-	pF	
Gate Resistance	R_g	-	9.45	-	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_g	-	15.4	-	nC	V_{GS} = -4.5V, V_{DS} = -10V, I_D = -4A
Gate-Source Charge	Q_{gs}	-	2.5	-	nC	
Gate-Drain Charge	Q_{gd}	-	3.3	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	16.8	-	ns	V_{DS} = -10V, V_{GS} = -4.5V, R_L = 10Ω, R_G = 6.0Ω, I_D = -1A
Turn-On Rise Time	t_r	-	12.4	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	94.1	-	ns	
Turn-Off Fall Time	t_f	-	42.4	-	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effects.
6. Guaranteed by design. Not subject to production testing.

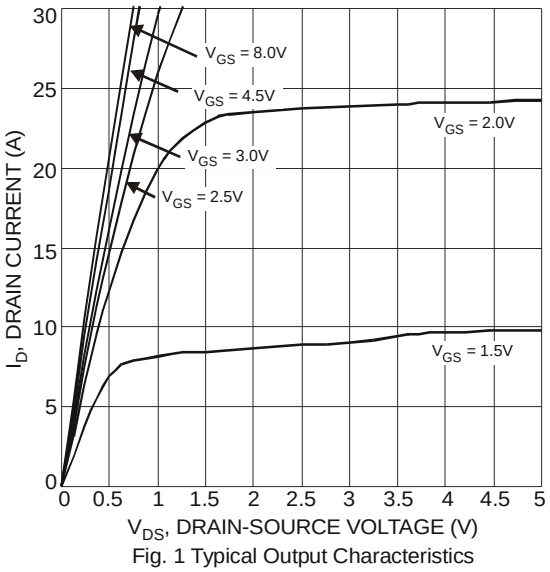


Fig. 1 Typical Output Characteristics

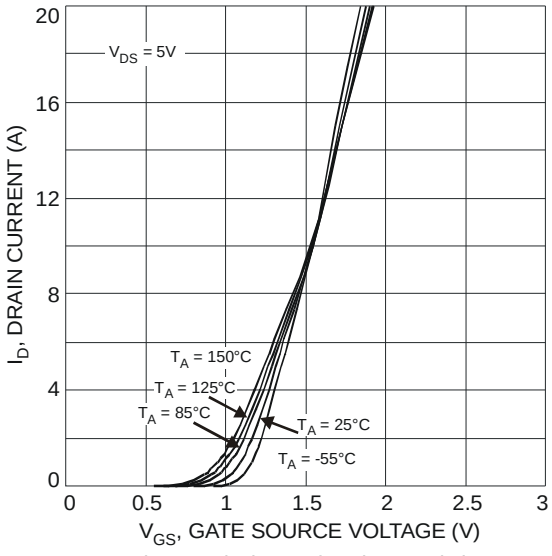


Fig. 2 Typical Transfer Characteristics

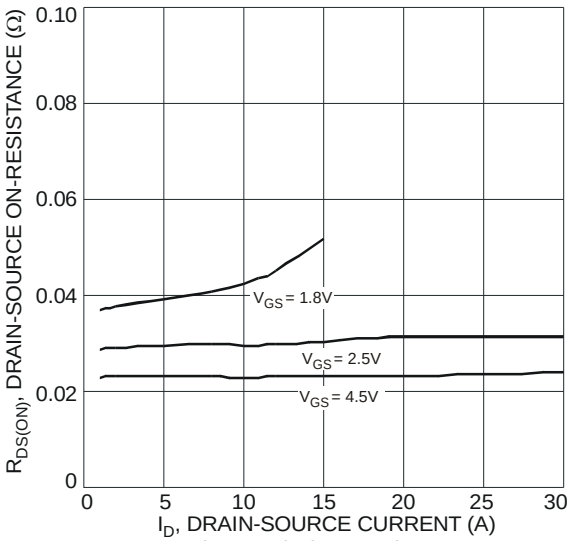


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

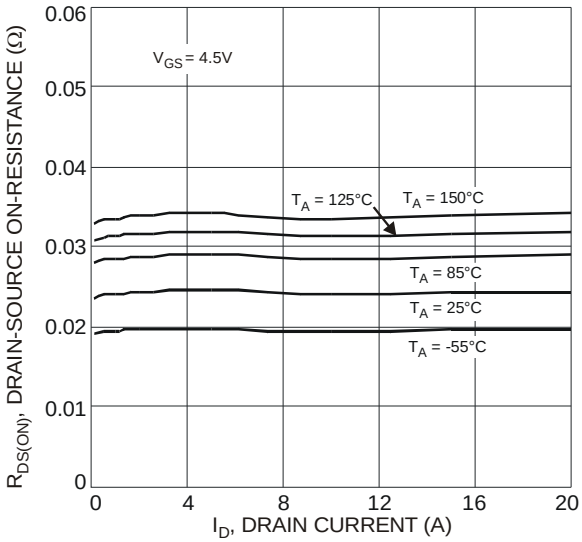


Fig. 4 Typical Drain-Source On-Resistance
vs. Drain Current and Temperature

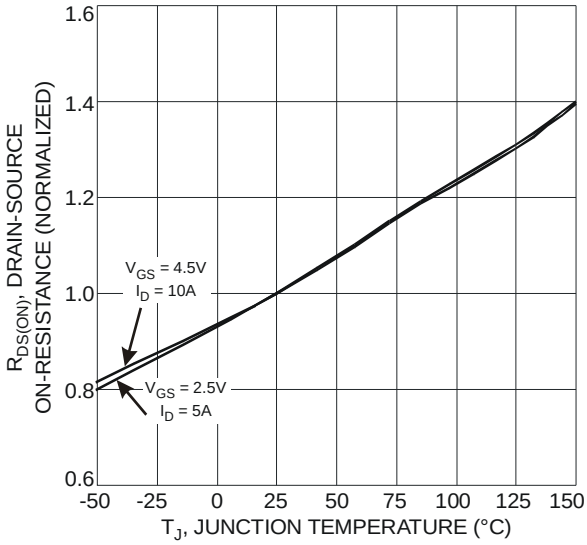


Fig. 5 On-Resistance Variation with Temperature

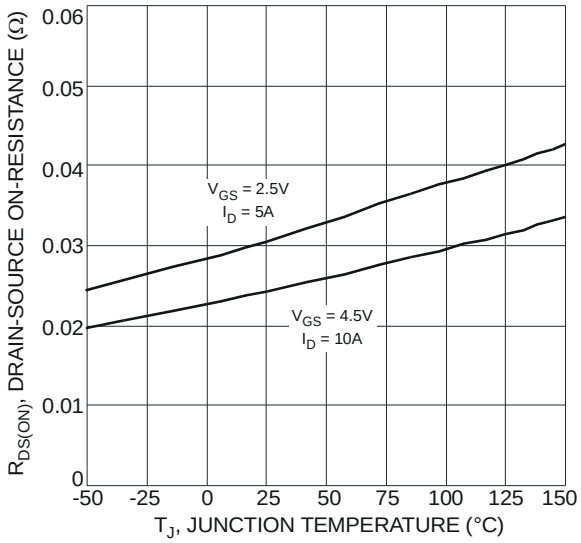


Fig. 6 On-Resistance Variation with Temperature

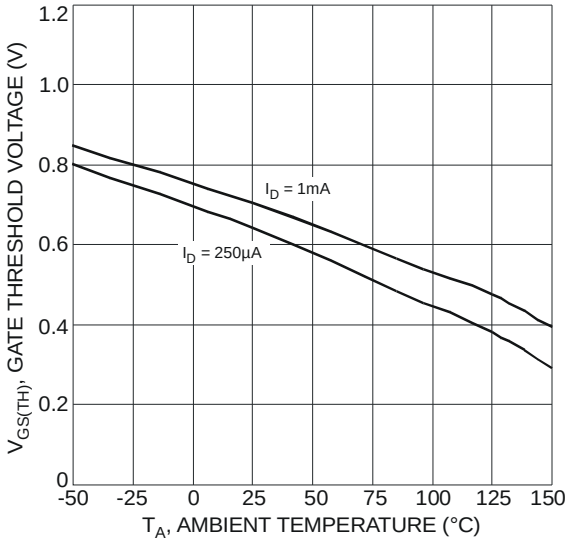


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

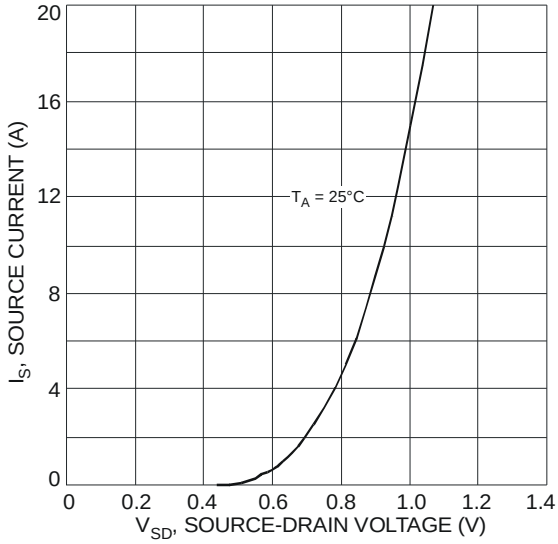


Fig. 8 Diode Forward Voltage vs. Current

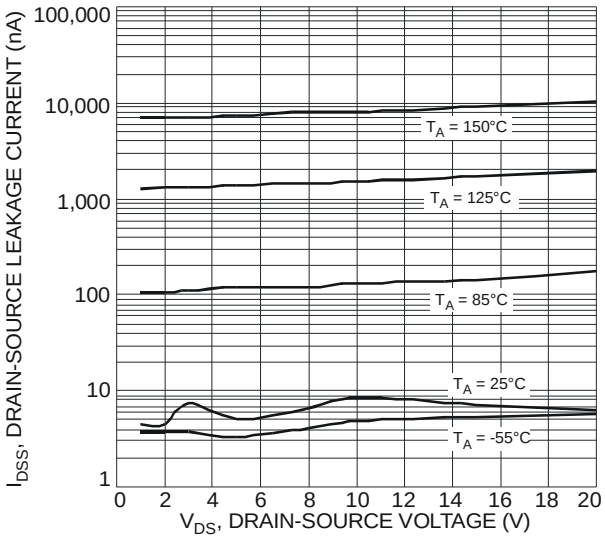


Fig. 9 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

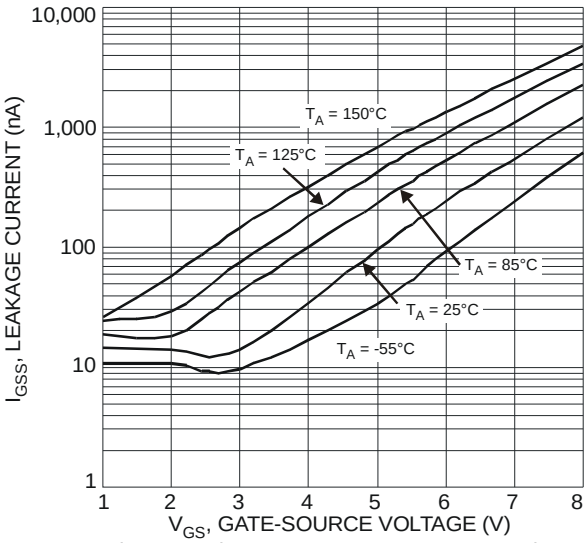


Fig. 10 Leakage Current vs. Gate-Source Voltage

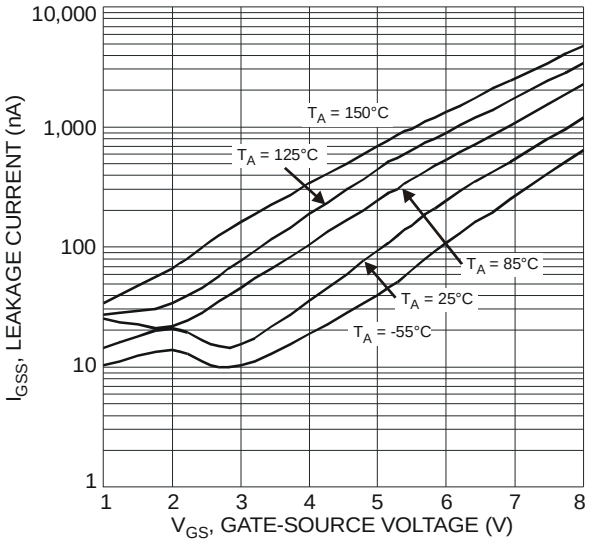


Fig. 11 Leakage Current vs. Gate-Source Voltage

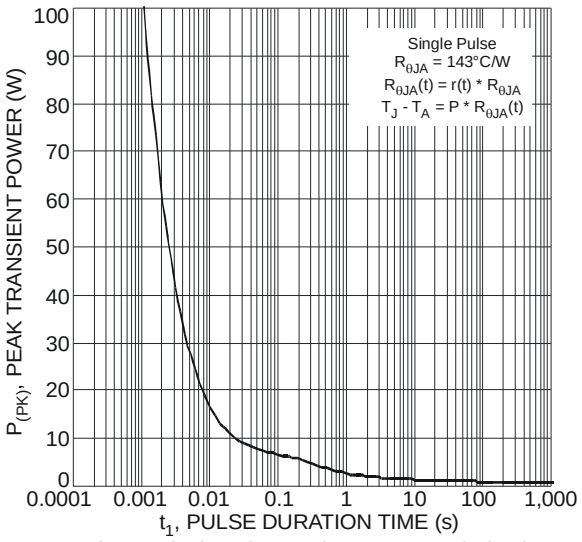


Fig. 12 Single Pulse Maximum Power Dissipation

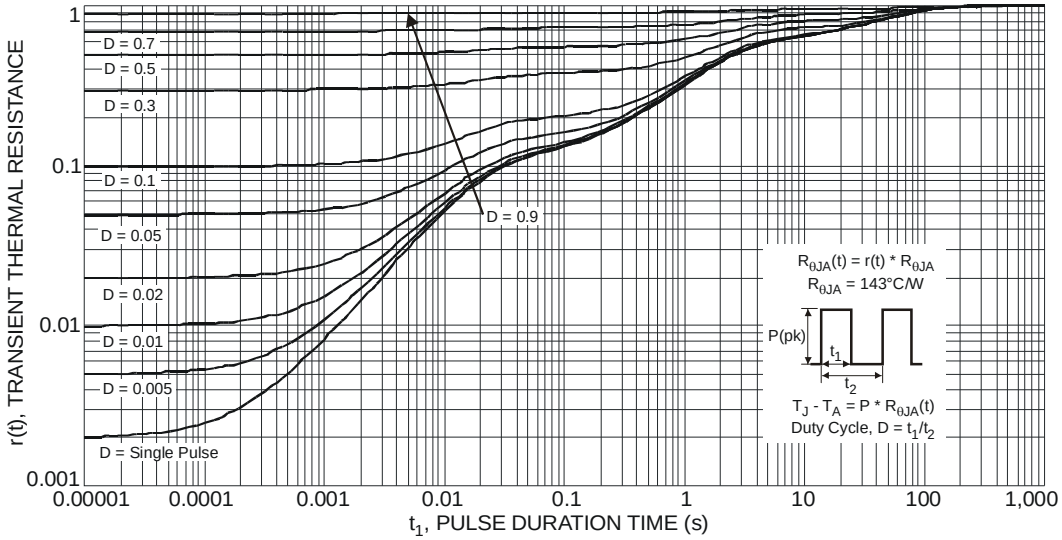
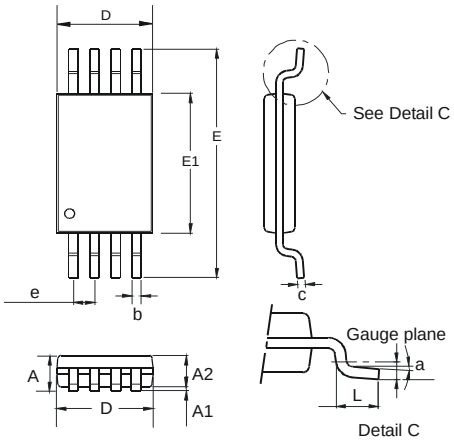


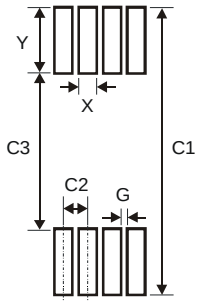
Fig. 13 Transient Thermal Response

Package Outline Dimensions



TSSOP-8L			
Dim	**Min**	**Max**	**Typ**
a	0.09	–	–
A	–	1.20	–
A1	0.05	0.15	–
A2	0.825	1.025	0.925
b	0.19	0.30	–
c	0.09	0.20	–
D	2.90	3.10	3.025
e	–	–	0.65
E	–	–	6.40
E1	4.30	4.50	4.425
L	0.45	0.75	0.60
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.45
Y	1.78
C1	7.72
C2	0.65
C3	4.16
G	0.20